

M.2 (S42)

3IE3 Series

Customer: _____

Customer

Part

Number: _____

Innodisk

Part

Number: _____

Innodisk

Model Name: _____

Date: _____

Innodisk Approver	Customer Approver

**Total Solution For
Industrial Flash Storage**

Table of contents

LIST OF FIGURES	6
1. PRODUCT OVERVIEW	7
1.1 INTRODUCTION OF INNODISK M.2 (S42) 3IE3	7
1.2 PRODUCT VIEW AND MODELS	7
1.3 SATA INTERFACE	7
2. PRODUCT SPECIFICATIONS	8
2.1 CAPACITY AND DEVICE PARAMETERS	8
2.2 PERFORMANCE	8
2.3 ELECTRICAL SPECIFICATIONS	8
2.3.1 Power Requirement	8
2.3.2 Power Consumption	9
2.4 ENVIRONMENTAL SPECIFICATIONS	9
2.4.1 Temperature Ranges	9
2.4.2 Humidity	9
2.4.3 Shock and Vibration	9
2.4.4 Mean Time between Failures (MTBF)	9
2.5 CE AND FCC COMPATIBILITY	10
2.6 RoHS COMPLIANCE	10
2.7 RELIABILITY	10
2.8 TRANSFER MODE	10
2.9 PIN ASSIGNMENT	10
2.10 MECHANICAL DIMENSIONS	12
2.11 ASSEMBLY WEIGHT	12
2.12 SEEK TIME	12
2.13 HOT PLUG	12
2.14 NAND FLASH MEMORY	12
3. THEORY OF OPERATION	13
3.1 OVERVIEW	13
3.2 SATA III CONTROLLER	13
3.3 ERROR DETECTION AND CORRECTION	14
3.4 WEAR-LEVELING	14
3.5 BAD BLOCKS MANAGEMENT	14
3.6 POWER CYCLING	14
3.7 GARBAGE COLLECTION	14
4. INSTALLATION REQUIREMENTS	15
4.1 M.2 (S42) 3IE3 PIN DIRECTIONS	15

4.2 ELECTRICAL CONNECTIONS FOR M.2 (S42) 3IE3	15
4.3 DEVICE DRIVE	15
5. PART NUMBER RULE	16
APPENDIX	17

REVISION HISTORY

Revision	Description	Date
Rev1.0	First Released	Feb., 2016
Rev1.1	Update performance/mechanical drawing/ Modify pin assignment/ power consumption Update RoHS/REACH certification	Nov.,2017
Rev1.2	Modify the TBW	Mar., 2022

List of Tables

TABLE 1: DEVICE PARAMETERS	8
TABLE 2: PERFORMANCE	8
TABLE 3: INNODISK M.2 (S42) 3IE3 POWER REQUIREMENT	8
TABLE 4: POWER CONSUMPTION	9
TABLE 5: TEMPERATURE RANGE FOR M.2 (S42) 3IE3	9
TABLE 6: SHOCK/VIBRATION TESTING FOR M.2 (S42) 3IE3	9
TABLE 7: M.2 (S42) 3IE3 MTBF	10
TABLE 8: INNODISK M.2 (S42) 3IE3 PIN ASSIGNMENT	11

List of Figures

FIGURE 1: INNODISK M.2 (S42) 3IE3 (TYPE 2242)	7
FIGURE 2: INNODISK M.2 (S42) 3IE3 BLOCK DIAGRAM	13
FIGURE 3: SIGNAL SEGMENT AND POWER SEGMENT	15

1. Product Overview

1.1 Introduction of Innodisk M.2 (S42) 3IE3

Innodisk M.2 (S42) 3IE3 is designed as the standard M.2 form factor with SATA interface, and supports SATA III standard (6.0Gb/s) with excellent performance. The form factor refers to the M.2(NGFF) specification which established by JEDEC. Regarding of mechanical interference, Innodisk M.2 (S42) 3IE3 absolutely replaces the traditional hard disk and makes personal computer, in any field, smaller and easier.

Innodisk M.2 (S42) 3IE3 effectively reduces the booting time of operation system and the power consumption is less than hard disk drive (HDD), and complies with ATA protocol, no additional drives are required, and can be configured as a boot device or data storage device

1.2 Product View and Models

Innodisk M.2 (S42) 3IE3 is available in follow capacities within MLC flash ICs.

[M.2 \(S42\) 3IE3 08GB \(type 2242\)](#)

[M.2 \(S42\) 3IE3 16GB \(type 2242\)](#)

[M.2 \(S42\) 3IE3 32GB \(type 2242\)](#)

[M.2 \(S42\) 3IE3 64GB \(type 2242\)](#)



Figure 1: Innodisk M.2 (S42) 3IE3 (type 2242)

1.3 SATA Interface

Innodisk M.2 (S42) 3IE3 supports SATA III interface, and compliant with SATA I and SATA II. SATA III interface can work with Serial Attached SCSI (SAS) host system, which is used in server computer. Innodisk M.2 (S42) 3IE3 is compliant with Serial ATA Gen 1, Gen 2 and Gen 3 specification (Gen 3 supports 1.5Gbps /3.0Gbps/6.0Gbps data rate).

2. Product Specifications

2.1 Capacity and Device Parameters

M.2 (S42) 3IE3 device parameters are shown in Table 1.

Table 1: Device parameters

Capacity	Cylinders	Heads	Sectors	LBA	User Capacity (MB)
8GB	15525	16	63	15649200	7641
16GB	16383	16	63	31277232	15272
32GB	16383	16	63	62533296	30533
64GB	16383	16	63	125045424	61057

2.2 Performance

Burst Transfer Rate: 6.0Gbps

Table 2: Performance

Capacity	8GB	16GB	32GB	64GB
Sequential* Read (max.)	110 MB/s	210 MB/s	240 MB/s	240 MB/s
Sequential* Write (max.)	50 MB/s	100 MB/s	160 MB/s	160 MB/s
4KB Random** Read (QD32)	5400 IOPS	8000 IOPS	9100 IOPS	9100 IOPS
4KB Random** Write (QD32)	12400 IOPS	20000 IOPS	25300 IOPS	25300 IOPS

Note: * Sequential performance is based on CrystalDiskMark 3.03 with file size 1000MB

** Random performance is based on CrystalDiskMark 3.03 with Queue Depth 32

2.3 Electrical Specifications

2.3.1 Power Requirement

Table 3: Innodisk M.2 (S42) 3IE3 Power Requirement

Item	Symbol	Rating	Unit
Input voltage	V _{IN}	+3.3 DC +- 5%	V

2.3.2 Power Consumption

Table 4: Power Consumption

Mode	Power Consumption (mA)
Read	300 (max.)
Write	370 (max.)
Idle	140 (max.)

* Target: 64GB M.2 (S42) 3IE3

2.4 Environmental Specifications

2.4.1 Temperature Ranges

Table 5: Temperature range for M.2 (S42) 3IE3

Temperature	Range
Operating	Standard Grade: 0°C to +70°C
	Industrial Grade: -40°C to +85°C
Storage	-40°C to +85°C

2.4.2 Humidity

Relative Humidity: 10-95%, non-condensing

2.4.3 Shock and Vibration

Table 6: Shock/Vibration Testing for M.2 (S42) 3IE3

Reliability	Test Conditions	Reference Standards
Vibration	7 Hz to 2K Hz, 20G, 3 axes	IEC 68-2-6
Mechanical Shock	Duration: 0.5ms, 1500 G, 3 axes	IEC 68-2-27

2.4.4 Mean Time between Failures (MTBF)

Table 7 summarizes the MTBF prediction results for various M.2 (S42) 3IE3 configurations. The analysis was performed using a RAM Commander™ failure rate prediction.

- **Failure Rate:** The total number of failures within an item population, divided by the total number of life units expended by that population, during a particular measurement interval under stated condition.
- **Mean Time between Failures (MTBF):** A basic measure of reliability for repairable items: The mean number of life units during which all parts of the item perform within their specified limits, during a particular measurement interval under stated conditions.

Table 7: M.2 (S42) 3IE3 MTBF

Product	Condition	MTBF (Hours)
Innodisk M.2 (S42) 3IE3	Telcordia SR-332 GB, 25°C	>3,000,000

2.5 CE and FCC Compatibility

M.2 (S42) 3IE3 conforms to CE and FCC requirements.

2.6 RoHS Compliance

M.2 (S42) 3IE3 is fully compliant with RoHS directive.

2.7 Reliability

Parameter		Value
Read Cycles		Unlimited Read Cycles
Flash endurance		20,000 P/E cycles
Wear-Leveling Algorithm		Support
Bad Blocks Management		Support
Error Correct Code		Support
TBW* (Total Bytes Written) Unit: TB		
Capacity	Sequential workload	Client workload
8GB	142	21.7
16GB	284	43.4
32GB	568	86.8
64GB	1136	173.6
128GB	2272	347.2
256GB	4544	694.4
* Note:		
1. Sequential: Mainly sequential write, tested by Vdbench.		
2. Client: Follow JESD218 Test method and JESD219A Workload, tested by ULINK. (The capacity lower than 64GB client workload is not specified in JEDEC219A, the values are estimated.)		
3. Based on out-of-box performance.		

2.8 Transfer Mode

M.2 (S42) 3IE3 support following transfer mode:

Serial ATA III 6.0Gbps

Serial ATA II 3.0Gbps

Serial ATA I 1.5Gbps

2.9 Pin Assignment

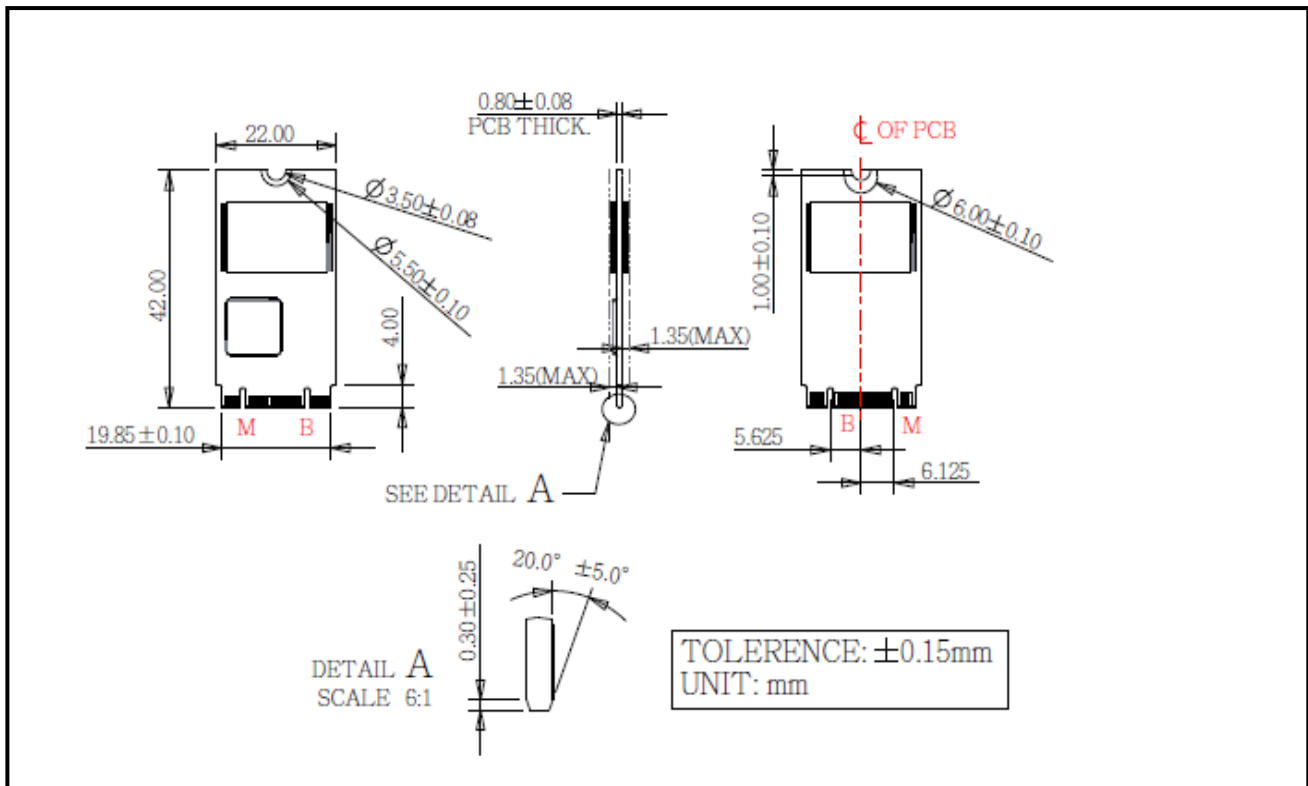
Innodisk M.2 (S42) 3IE3 uses a standard SATA pin-out. See Table 8 for M.2 (S42) 3IE3 pin assignment.

Table 8: Innodisk M.2 (S42) 3IE3 Pin Assignment

Signal Name	Pin #	Pin #	Signal Name
		75	GND
3.3V	74	73	GND
3.3V	72	71	GND
3.3V	70	69	GND
NC	68	67	NC
Notch	66	65	Notch
Notch	64	63	Notch
Notch	62	61	Notch
Notch	60	59	Notch
Reserved/MFG Clock	58		
Reserved/ MFG Data	56	57	GND
NC	54	55	NC
NC	52	53	NC
NC	50	51	GND
NC	48	49	RX+
NC	46	47	RX-
NC	44	45	GND
NC	42	43	TX-
NC	40	41	TX+
NC	38	39	GND
NC	36	37	NC
NC	34	35	NC
NC	32	33	GND
NC	30	31	NC
NC	28	29	NC
NC	26	27	GND
NC	24	25	NC
NC	22	23	NC
NC	20	21	GND
Notch	18	19	Notch
Notch	16	17	Notch
Notch	14	15	Notch
Notch	12	13	Notch
DAS/DSS	10	11	NC
NC	8	9	NC
NC	6	7	NC
3.3V	4	5	NC

3.3V	2	3	GND
		1	GND

2.10 Mechanical Dimensions



2.11 Assembly Weight

An Innodisk M.2 (S42) 3IE3 within flash ICs, 64GB's weight is 8 grams approximately.

2.12 Seek Time

Innodisk M.2 (S42) 3IE3 is not a magnetic rotating design. There is no seek or rotational latency required.

2.13 Hot Plug

The SSD support hot plug function and can be removed or plugged-in during operation. User has to avoid hot plugging the SSD which is configured as boot device and installed operation system.

Surprise hot plug : The insertion of a SATA device into a backplane (combine signal and power) that has power present. The device powers up and initiates an OOB sequence.

Surprise hot removal: The removal of a SATA device from a powered backplane, without first being placed in a quiescent state.

2.14 NAND Flash Memory

Innodisk M.2 (S42) 3IE3 uses Multi Level Cell (MLC) NAND flash memory, which is non-volatility, high reliability and high speed memory storage.

3. Theory of Operation

3.1 Overview

Figure 2 shows the operation of Innodisk M.2 (S42) 3IE3 from the system level, including the major hardware blocks.

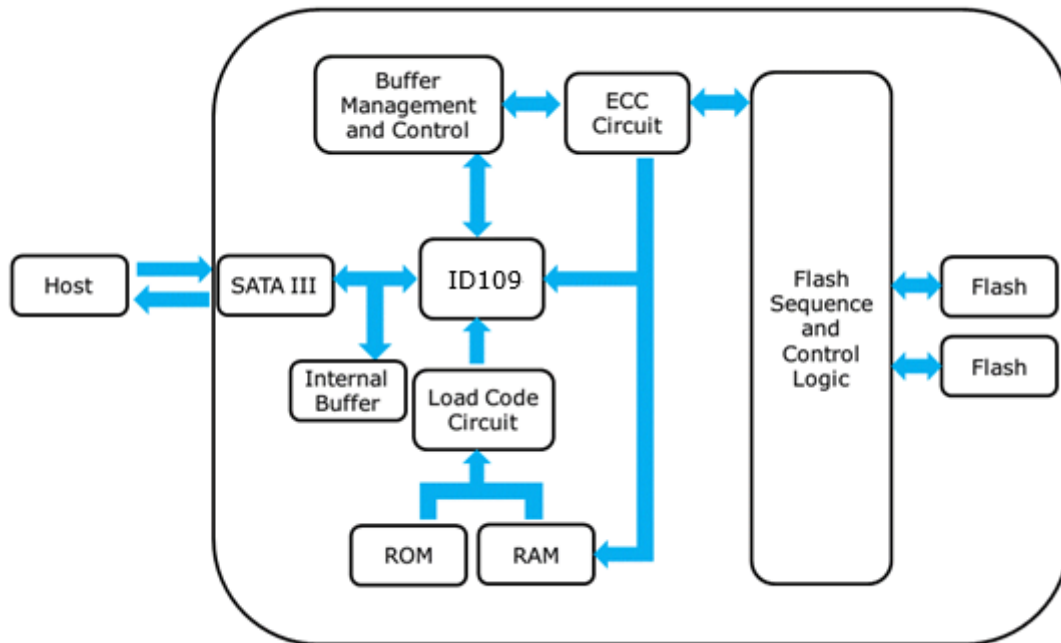


Figure 2: Innodisk M.2 (S42) 3IE3 Block Diagram

Innodisk M.2 (S42) 3IE3 integrates a SATA III controller and NAND flash memories. Communication with the host occurs through the host interface, using the standard ATA protocol. Communication with the flash device(s) occurs through the flash interface.

3.2 SATA III Controller

Innodisk M.2 (S42) 3IE3 is designed with ID 109, a SATA III 6.0Gbps (Gen. 3) controller. The Serial ATA physical, link and transport layers are compliant with Serial ATA Gen 1, Gen 2 and Gen 3 specification (Gen 3 supports 1.5Gbps/3.0Gbps/6.0Gbps data rate). The controller has 2 channels for flash interface.

3.3 Error Detection and Correction

Highly sophisticated Error Correction Code algorithms are implemented. The ECC unit consists of the Parity Unit (parity-byte generation) and the Syndrome Unit (syndrome-byte computation). This unit implements an algorithm that can correct 40 bits per 1024 bytes in an ECC block. Code-byte generation during write operations, as well as error detection during read operation, is implemented on the fly without any speed penalties.

3.4 Wear-Leveling

Flash memory can be erased within a limited number of times. This number is called the **erase cycle limit** or **write endurance limit** and is defined by the flash array vendor. The erase cycle limit applies to each individual erase block in the flash device.

Innodisk M.2 (S42) 3IE3 uses a static wear-leveling algorithm to ensure that consecutive writes of a specific sector are not written physically to the same page/block in the flash. This spreads flash media usage evenly across all pages, thereby extending flash lifetime.

3.5 Bad Blocks Management

Bad Blocks are blocks that contain one or more invalid bits whose reliability are not guaranteed. The Bad Blocks may be presented while the SSD is shipped, or may develop during the life time of the SSD. When the Bad Blocks is detected, it will be flagged, and not be used anymore. The SSD implement Bad Blocks management, Bad Blocks replacement, Error Correct Code to avoid data error occurred. The functions will be enabled automatically to transfer data from Bad Blocks to spare blocks, and correct error bit.

3.6 Power Cycling

Innodisk's power cycling management is a comprehensive data protection mechanism that functions before and after a sudden power outage to SSD. Low-power detection terminates data writing before an abnormal power-off, while table-remapping after power-on deletes corrupt data and maintains data integrity. Innodisk's power cycling provides effective power cycling management, preventing data stored in flash from degrading with use.

3.7 Garbage Collection

Garbage collection is used to maintain data consistency and perform continual data cleansing on SSDs. It runs as a background process, freeing up valuable controller resources while sorting good data into available blocks, and deleting bad blocks. It also significantly reduces write operations to the drive, thereby increasing the SSD's speed and lifespan.

4. Installation Requirements

4.1 M.2 (S42) 3IE3 Pin Directions

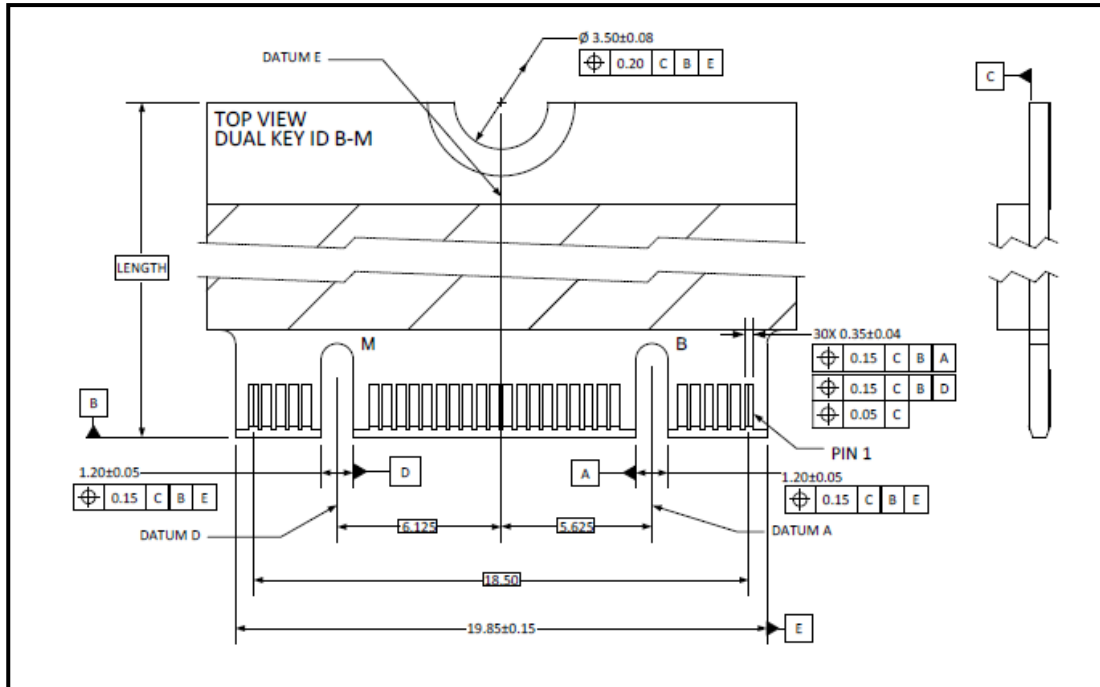


Figure 3: Signal Segment and Power Segment

4.2 Electrical Connections for M.2 (S42) 3IE3

A Serial ATA device may be either directly connected to a host or connected to a host through a cable. For connection via cable, the cable should be no longer than 1meter. The SATA interface has a separate connector for the power supply. Please refer to the pin description for further details.

4.3 Device Drive

No additional device drives are required. The Innodisk M.2 (S42) 3IE3 can be configured as a boot device.

5. Part Number Rule

CODE	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16	17	18	19	20	21	
	D	H	M	2	4	-	3	2	G	D	0	9	B	C	1	D	C	-	X	X	X	
Definition																						
Code 1st~2nd (Disk)											Code 14th (Operation Temperature)											
DH : Embedded Disk(iSLC)											C: Standard Grade (0°C ~ +70°C)											
											W: Industrial Grade (-40°C ~ +85°C)											
Code 3rd ~5th (Form factor)											Code 15th (Internal control)											
M24: M.2-SATA Type 2242											1~9: TSOP PCB version.											
Code 7th ~9th (Capacity)											Code 16th (Channel of data transfer)											
S: Single Channel																						
08G: 8GB			16G: 16GB.			32G: 32GB			64G: 64GB			D: Dual Channels										
Code 10th ~12th (Controller)											Code 17th (Flash Type)											
D09: ID109											C: Toshiba MLC											
Code 13th (Flash mode)											Code 19th~21st (Customize code)											
B: Synchronous NAND for Toshiba 15nm																						

Appendix

RoHS



宜鼎國際股份有限公司 Innodisk Corporation

Page 1/1

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RoHS 自我宣告書 (RoHS Declaration of Conformity)

Manufacturer Product: All Innodisk EM Flash and Dram products

- 一、宜鼎國際股份有限公司（以下稱本公司）特此保證售予貴公司之所有產品，皆符合歐盟 2011/65/EU 及 (EU) 2015/863 關於 RoHS 之規範要求。

Innodisk Corporation declares that all products sold to the company, are complied with European Union RoHS Directive (2011/65/EU) and (EU) 2015/863 requirement.

- 二、本公司同意因本保證書或與本保證書相關事宜有所爭議時，雙方宜友好協商，達成協議。

Innodisk Corporation agrees that both parties shall settle any dispute arising from or in connection with this Declaration of Conformity by friendly negotiations.

Name of hazardous substance	Limited of RoHS ppm (mg/kg)
鉛 (Pb)	< 1000 ppm
汞 (Hg)	< 1000 ppm
鎘 (Cd)	< 100 ppm
六價鉻 (Cr 6+)	< 1000 ppm
多溴聯苯 (PBBs)	< 1000 ppm
多溴二苯醚 (PBDEs)	< 1000 ppm
鄰苯二甲酸二(2-乙基己基)酯 (DEHP)	< 1000 ppm
鄰苯二甲酸丁酯苯甲酯 (BBP)	< 1000 ppm
鄰苯二甲酸二丁酯 (DBP)	< 1000 ppm
鄰苯二甲酸二異丁酯 (DIBP)	< 1000 ppm

立保證書人 (Guarantor)

Company name 公司名稱：Innodisk Corporation 宜鼎國際股份有限公司

Company Representative 公司代表人：Randy Chien 顏川陸

Company Representative Title 公司代表人職稱：Chairman 董事長

Date 日期：2017 / 01 / 18



REACH

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REACH Declaration of Conformity

Manufacturer Product: All Innodisk EM Flash and Dram products

1. 宜鼎國際股份有限公司（以下稱本公司）特此保證此售予貴公司之產品，皆符合歐盟化學品法案(Registration, Evaluation and Authorization of Chemicals: (EC) No 1907/2006 REACH) 以及附錄 XIV 中的限用物質之規定 (<http://www.echa.europa.eu/de/candidate-list-table> last updated: 12/01/2017, SVHC's 173)。

所提供之產品包含：(1) 產品或產品所使用到的所有原物料；(2) 包裝材料；(3) 設計、生產及重工過程中所使用到的所有原物料。

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Products include: 1) Product and raw material used by the product; 2) Packaging material; 3) Raw material used in the process of design, production and rework.

2. 本公司同意因本保證書或與本保證書相關事宜有所爭議時，雙方宜友好協商，達成協議。InnoDisk Corporation agrees that both parties shall settle any dispute arising from or in connection with this Declaration of Conformity by friendly negotiations.

立保證書人 (Guarantor)

Company name 公司名稱：InnoDisk Corporation 宜鼎國際股份有限公司

Company Representative 公司代表人：Randy Chien 簡川勝

Company Representative Title 公司代表人職稱：Chairman 董事長

Date 日期：2017 / 02 / 08



CE

ISL International Standards Laboratory http://www.isl.com.tw

Certificate

Issue Date: July 29, 2015
Ref. Report No. ISL-15LE321CE

Product Name : M.2
Model(s) : M.2 (S42) 3S*#-&
(S:Flash type: (S:SLC,I:ISLC,M:MLC);
*:Product line: (E:Embedded, G:EverGreen, R:InnoRobust);
#:Controller: (empty:106/107/167/170, 2:201/ 202, 3:108/109);
&:Product feature: (P:with DRAM, empty:without DRAM))
Responsible Party : Innodisk Corporation
Address : 5F.No.237, Sec. 1, Datong Rd., Xizhi Dist., New Taipei City 221, Taiwan
(R.O.C.)

We, International Standards Laboratory, hereby certify that:

The device bearing the trade name and model specified above has been shown to comply with the applicable technical standards as indicated in the measurement report and was tested in accordance with the measurement procedures specified in European Council Directive- EMC Directive 2004/108/EC. The device was passed the test performed according to :



Standards:

EN 55022: 2010+AC2011 and CISPR 22: 2008 (modified)
EN 61000-3-2: 2006+A1:2009 +A2:2009 and IEC 61000-3-2: 2005+A1:2008 +A2:2009
EN 61000-3-3: 2013 and IEC 61000-3-3: 2013
EN 55024: 2010 and CISPR 24: 2010
EN 61000-4-2: 2009 and IEC 61000-4-2: 2008
EN 61000-4-3: 2006+A1: 2008 +A2: 2010 and
IEC 61000-4-3:2006+A1: 2007+A2: 2010
EN 61000-4-4:2012 and IEC 61000-4-4:2012

I attest to the accuracy of data and all measurements reported herein were performed by me or were made under my supervision and are correct to the best of my knowledge and belief. I assume full responsibility for the completeness of these measurements and vouch for the qualifications of all persons taking them.

International Standards Laboratory

Jim Chu
Jim Chu / Director

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Tao Yuan City 325, Taiwan
Tel: 886-3-407-1718; Fax: 886-3-407-1738



FCC

ISL International Standards Laboratory Laboratory http://www.isl.com.tw

Certificate

Issue Date: July 29, 2015
Ref. Report No. ISL-15LE321FB

Product Name : M.2
Model(s) : M.2 (S42) 3S*#-&
(S:Flash type: (S:SLC,I:ISLC,M:MLC);
*:Product line: (E:Embedded, G:EverGreen, R:InnoRobust);
#:Controller: (empty:106/107/167/170, 2:201/ 202, 3:108/109);
&:Product feature: (P:with DRAM, empty:without DRAM))
Applicant : Innodisk Corporation
Address : 5F.No.237, Sec. 1, Datong Rd., Nizhi Dist., New Taipei City 221, Taiwan (R.O.C.)

We, International Standards Laboratory, hereby certify that:

The device bearing the trade name and model specified above has been shown to comply with the applicable technical standards as indicated in the measurement report and was tested in accordance with the measurement procedures specified. (refer to Test Report if any modifications were made for compliance).



Standards:

FCC CFR Title 47 Part 15 Subpart B: 2014- Section 15.107 and 15.109
ANSI C63.4-2009
Industry Canada Interference-Causing Equipment Standard ICES-003 Issue 5: 2012

Class B

I attest to the accuracy of data and all measurements reported herein were performed by me or were made under my supervision and are correct to the best of my knowledge and belief. I assume full responsibility for the completeness of these measurements and vouch for the qualifications of all persons taking them.

International Standards Laboratory

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